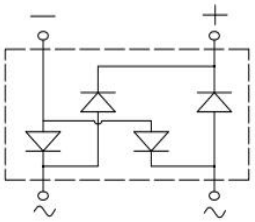
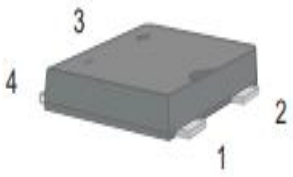
Bridge Rectifier Diode 整流桥





■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Reflow Solder Temperature 220℃ 回流焊温度 220 度
Package 封装: UMB

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	UM1B	UM2B	UM4B	UM6B	UM8B	UM10B	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	0.8						A
Peak Surge Current 峰值浪涌电流	I_{FSM}	25						A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	110						℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	150℃,-55to+150℃						

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	V_F		1 1.1		V	I_F=0.4A 0.8A
Reverse Current (T_A=25℃) 反向漏电流(T_A=125℃)	I_R			3 30	uA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D		13		pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

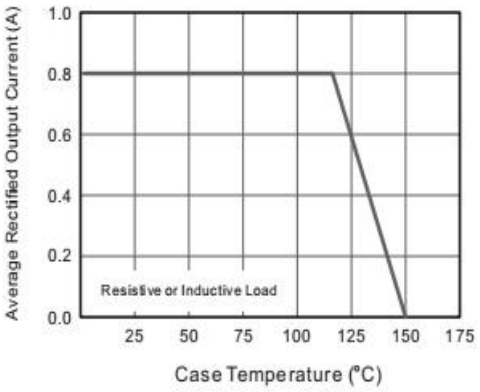


Figure 1: Forward Current Derating Curve

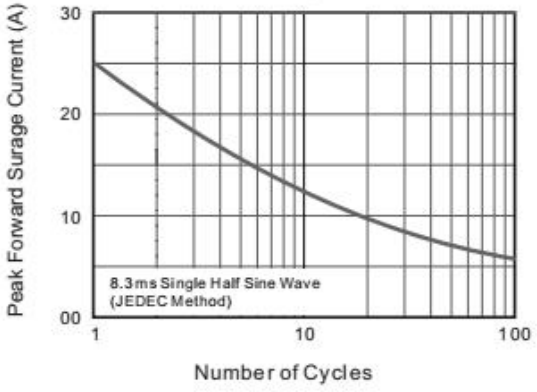


Figure 2: Peak Forward Surge Current

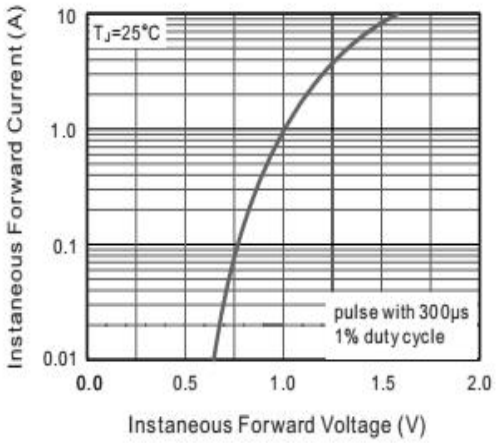


Figure 3:Instantaneous Forward Characteristics

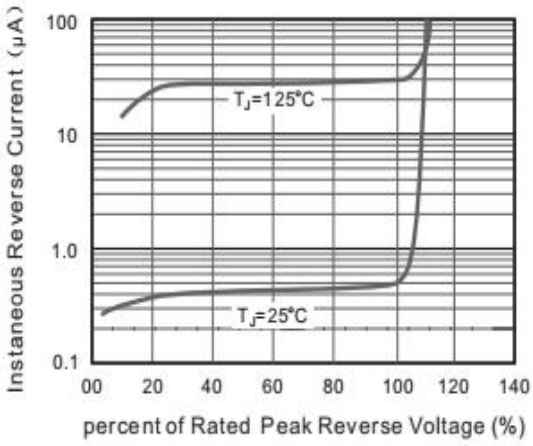


Figure 4: Reverse Leakage Characteristics

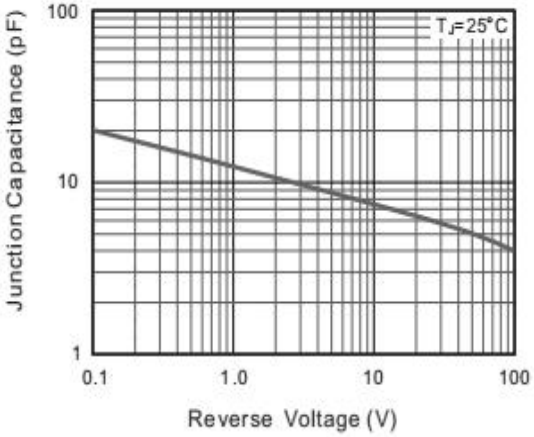
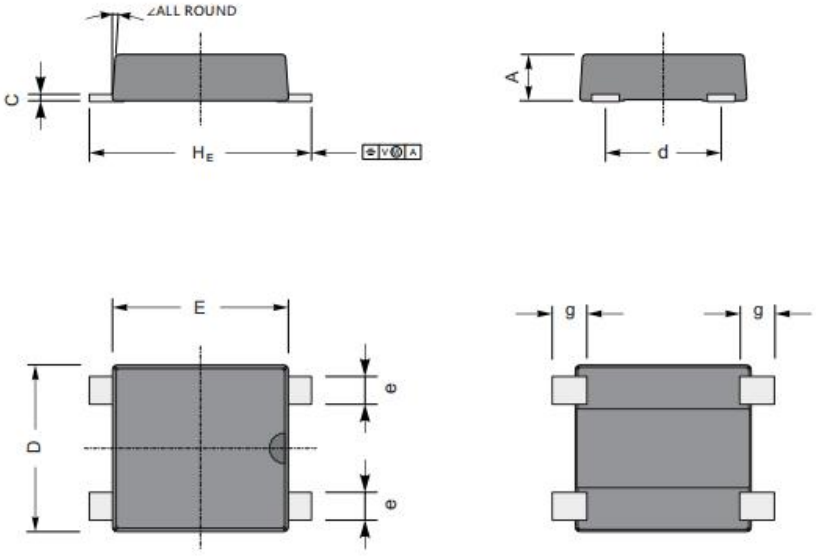


Figure 5: Junction Capacitance Characteristics

■Dimension 外形封装尺寸



UMB mechanical data

UNIT		A	C	D	E	H_E	g	d	e	∠
mm	max	1.2	0.20	3.8	4.0	5.1	0.82	2.7	0.70	7°
	min	1.0	0.12	3.4	3.6	4.6	0.51	2.3	0.51	
mil	max	47	7.9	150	157	201	32	106	28	
	min	39	4.7	134	142	181	20	91	20	